



Atty.
Dkt. No.

M#

Client Ref.

276665

F01-243-USDIV

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: MANABE

Appln. No.: 09/783,035

Filing Date: February 15, 2001

Date: June 11, 2002

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Examiner: Not Assigned

Group Art Unit: 2826

U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR						
	BR						
	CR						
	DR						
	ER						
	FR						
	GR						
	HR						
	IR						
	JR						
	KR						
	LR						

FOREIGN PATENT DOCUMENTS

		Document Number	Date MM/YYYY	Country	Inventor Name		Abstract		Readily Available	
							Enclosed	No	Enclose	No
Kc	MR	58-102865	12/1984	JAPAN	MAEBOTOKE et al.		x			
Kc	NR	06-209120	07/1994	JAPAN	NAKAMURA et al.		x			
	OR									
	PR									
	QR									
	RR									
	SR									
	TR									
	UR									
	VR									

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

	WR								
	XR								
	YR								
	ZR								
	AAR								
	BBR								

Examiner

K. Chutana

Date Considered:

6/16/2002

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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276665

F99-156-USDIV

INFORMATION DISCLOSURE STATEMENT
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Applicant: MANABE et al.

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Examiner: M. Tran

Group Art Unit: 2811

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Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
KC	AR 5,281,830	01/1994	KOTAKI et al.	—	—	
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KC	DR 5,408,120	04/1995	MANABE et al.	—	—	
	ER					

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						Enclosed	No	Enclose	No
KC	FR	599224	06/1994	EUROPE	NAKAMURA				
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KC	NR	2-229475	09/1990	JAPAN	MATSUOKA				
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KC	SR	Nakamura et al., "P-GaN/N-InGaN/N-GaN Double-Heterostructure Blue-Light-Emitting Diodes", Japanese J of Applied Physics, January 1993, Vol. 32, No. 1A/B, Part 2, pp. L8-L11.							
KC	TR	Nakamura et al., "Candela-class high-brightness InGaN/A1GaN double-heterostructure blue-light-emitting diodes", Applied Physics Letters, March 1994, Vol. 64, No. 13, pp. 1687-1689.							
KC	UR	Nakamura et al., "High-Brightness InGaN/A1GaN double-heterostructure blue-green-light-emitting diodes," J. of Applied Physics, December 1994, Vol. 76, No. 12, pp. 8189-8191.							
KC	VR	Khan et al., "Effects of Si On Photoluminescence of GaN", Solid State Communication, Vol. 57, No. 6, pp. 405-409, (1986).							
	WR	Matsushita et al., "PN Junction Type SiC Blue Light-Emitting Diodes", Applied Physics, Vol. 60, No. 2, pp. 159-162, Feb. 1991. <u>in Japanese only</u>							

Examiner

K. Chandra

Date Considered:

6/18/2002

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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**INFORMATION DISCLOSURE STATEMENT
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	JR					
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	LR					
	MR					
	NR					

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	OR							
	PR							
	QR							
	RR							
	SR							
	TR							

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XC	UR	Goldenberg et al., "Ultraviolet and violet light-emitting GaN diodes grown by low-pressure metalorganic chemical vapor deposition". Applied Physics Letters 62 (1993) 25 January, No. 4, New York, New York				
XC	VR	Nakamura et al., "High-power InGaN/GaN double-heterostructure violet light emitting diodes," Applied Physics Letters, Vol. 62, No. 19, May 10, 1993, pp. 2390-2392.				
XC	WR	Patent Abstracts of Japan, Vol. 018, No. 080 (E-1505), February 9, 1994 & JP 05 291621 A (Nichia Chem Ind Ltd.), November 5, 1993.				
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Examiner *XC*

Date Considered: 9/8/2002

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